

LS133

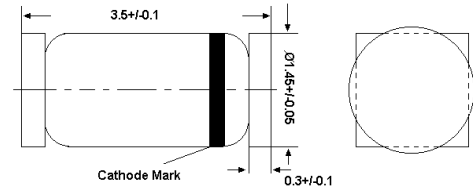
Silicon Epitaxial Planar Switching Diode

High speed switching diode

Features

- Glass sealed envelope
- High speed
- High reliability

LS-34



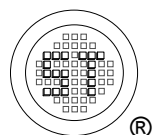
QuadroMELF
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	90	V
DC Reverse Voltage	V_R	80	V
Average Rectified Forward Current	$I_{F(AV)}$	130	mA
Peak Forward Current	I_{FM}	400	mA
Surge Forward Current (1 s)	I_{FSM}	600	mA
Power Dissipation	P_{tot}	300	mW
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 175	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100$ mA	V_F	1.2	V
Reverse Current at $V_R = 80$ V	I_R	0.5	μA
Capacitance Between Terminals at $V_R = 0.5$ V, $f = 1$ MHz	C_T	2	pF
Reverse Recovery Time at $V_R = 6$ V, $I_F = 10$ mA, $R_L = 50 \Omega$	t_{rr}	4	ns



Dated :15/06/2009